
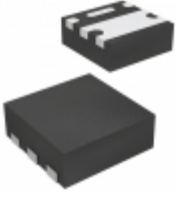


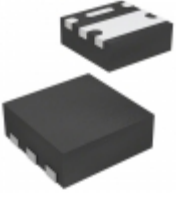



	<h2>SIA429DJT-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIA429DJT-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 12A SC-70</p> <p>Datenblätter:  SIA429DJT-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 22650 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIA429DJT-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 12A SC-70
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	22650 pcs Stock
detaillierte Beschreibung	P-Channel 20V 12A (Tc) 3.5W (Ta), 19W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SC-70-6
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Single
Verlustleistung (max)	3.5W (Ta), 19W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Tc)
Rds On (Max) @ Id, Vgs	20.5 mOhm @ 6A, 4.5V
VGS (th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	62nC @ 8V
Eingabekapazität (Ciss) (Max) @ Vds	1750pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	1.5V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIA429DJT-T1-GE3CT

SIA429DJT-T1-GE3 ist neu im Original, Suche SIA429DJT-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA429DJT-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIA429DJT-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIA427DJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 8V 12A SC-70-6</p>	 <p>SIA430DJ-T1-E3 VISHAY VISHAY QFN-6</p>	 <p>SIA430DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 12A SC70-6</p>	 <p>SIA430DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 20V 12A SC70-6</p>
 <p>SIA430DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 12A SC70-6</p>	 <p>SIA429DJT-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 12A SC-70</p>	 <p>SIA427ADJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 8V 12A 6SC-70</p>	 <p>SIA427ADJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 8V 12A 6SC-70</p>

heiße Teile

Mehr

SIA406DJ-T1-GE3	SIA408DJ-T1-GE3	SIA408DJ-T1-GE3	SIA411DJ-T1-GE3	SIA411DJ-T1-GE3
SIA413DJ-T1-GE3	SIA413DJ-T1-GE3	SIA413DJ-T4-GE3	SIA414DJ-T1-GE3	SIA414DJ-T1-GE3
SIA415DJ-T1-GE3	SIA415DJ-T1-GE3	SIA417DJ-T1-GE3	SIA417DJ-T1-GE3	SIA419DJ
SIA419DJ-T1-GE3	SIA419DJ-T1-GE3	SIA421DJ-T1-GE3	SIA421DJ-T1-GE3	SIA425EDJ-T1-GE3
SIA425EDJ-T1-GE3	SIA426DJ-T1-GE3	SIA426DJ-T1-GE3	SIA427DJ-T1-GE3	SIA427DJ-T1-GE3
SIA429DJT-T1-GE3	SIA430DJ-T1-GE3	SIA430DJ-T1-GE3	SIA431DJ	SIA431DJ-T1
SIA431DJ-T1-GE3	SIA431DJ-T1-GE3	SIA432DJ-T1-GE3	SIA432DJ-T1-GE3	SIA433EDJ
SIA433EDJ-T1-GE3	SIA433EDJ-T1-GE3	SIA436DJ-T1-GE3	SIA436DJ-T1-GE3	SIA443DJ-T1-GE3
SIA443DJ-T1-GE3	SIA444DJ-T1-GE3	SIA444DJ-T1-GE3	SIA445EDJ-T1-GE3	SIA445EDJ-T1-GE3
SIA447DJ-T1-GE3	SIA447DJ-T1-GE3	SIA448DJ-T1-GE3	SIA448DJ-T1-GE3	SIA449DJ-GE3

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